TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC3324

Audio Frequency Low Noise Amplifier Applications

Unit: mm

• High voltage: VCEO = 120 V

• Excellent hFE linearity: hFE (IC = 0.1 mA)/ hFE (IC = 2 mA) = 0.95 (typ.)

• High hfe: hfe = $200 \sim 700$

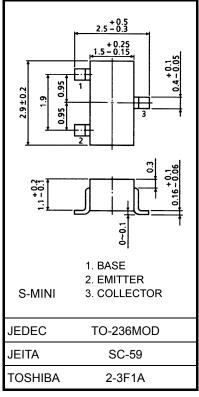
• Low noise: NF (2) = 0.2dB (typ.), 3dB (max)

• Complementary to 2SA1312

• Small package

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	120	V	
Collector-emitter voltage	V _{CEO}	120	V	
Emitter-base voltage	V _{EBO}	5	V	
Collector current	IC	100	mA	
Base current	ΙΒ	20	mA	
Collector power dissipation	PC	150	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T _{stg}	-55~125	°C	



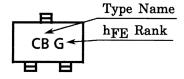
Weight: 0.012 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking

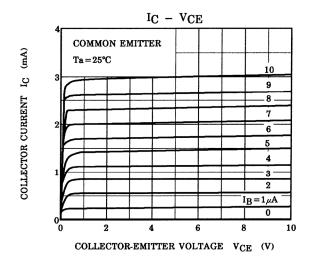


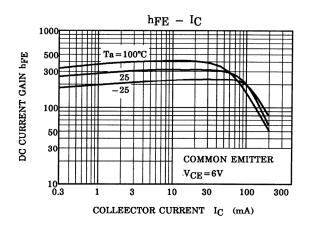
Electrical Characteristics (Ta = 25°C)

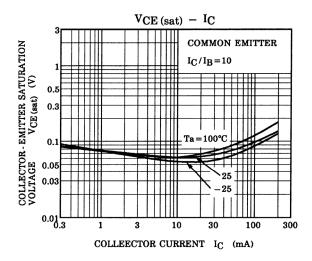
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current	I _{CBO}	V _{CB} = 120 V, I _E = 0	_	_	0.1	μА	
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	0.1	μА	
DC current gain	h _{FE} (Note)	V _{CE} = 6 V, I _C = 2 mA	200	_	700		
Collector-emitter saturation voltage	V _{CE} (sat)	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$	_	_	0.3	V	
Transition frequency	f _T	V _{CE} = 6 V, I _C = 1 mA	_	100	_	MHz	
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	3	_	pF	
Noise figure	NF (1)	V_{CB} = 6 V, I_{C} = 0.1 mA, f = 100 Hz, Rg = 10 k Ω	_	0.5	6	dB	
	NF (2)	V_{CB} = 6 V, I_{C} = 0.1 mA, f = 1 kHz, Rg = 10 k Ω	_	0.2	3	ub	

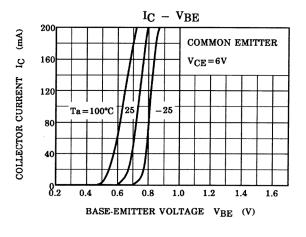
Note: hFE classification GR (G): 200~400, BL (L): 350~700

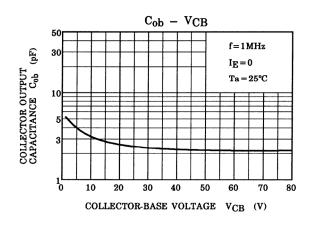
() marking symbol

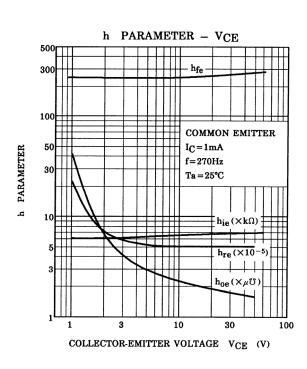


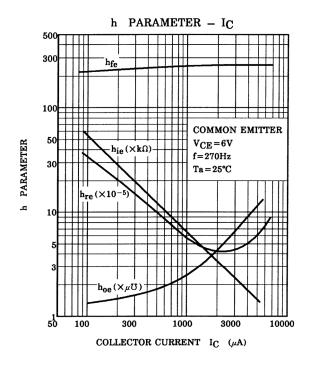


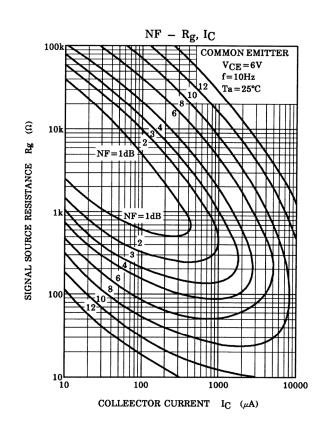


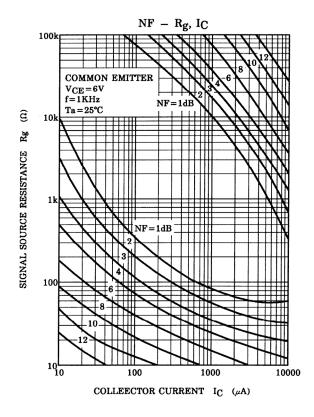


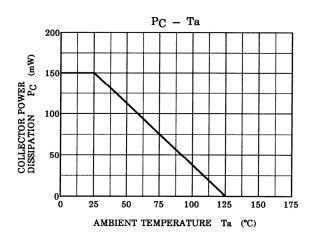












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20070701-EN GENERAL

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